

Technical Specifications

Magnetoresistive Device - type "IM_700"

Date : 27/02/2003

Parameter	Value	Comments
Substrate		
Composition	Sital	Commercial
Thickness	0.6 μm	
Length	19 mm	After cutting
Width	2 mm	After cutting
Sensitive Layer		
Composition	82.8%Ni-17.2%Fe	Commercial, Diode R.F. sputtering
Width	70 μm	
Length	14.3 mm	
Thickness	about 189 nm	Adjustable to R^0
Resistance at 0 Oe (R^0)	700 Ω +/- 10%	
Sensitivity at 10 Oe (S^{10})	not less than 1.0 %	Coplanar with the stripe and perpendicular to it.
Sensitivity at 20 Oe (S^{20})	not less than 1.5 %	same as above
Maximum Current		
	4 mA	Long term D.C.
Passivation layer		
Composition	SiO ₂ ~ 200 nm Solder Resist S02468NB	Magnetron sputtering for SiO ₂ . Screen-printing

Contact Pads (back side)	Square Configuration 1.5 x 1.5 mm	A tin bud deposited on each pad for easy soldering
Marking	Mark "MR700" identifying the type	Implemented on the top side by the photolithography mask

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